

**Notice of References Cited**Application/Control No.  
**09/838,892**Applicant(s)/Patent Under Reexam  
**Chu et al**Examiner  
**Savitri Mulpuri**Art Unit  
**2812**

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**U.S. PATENT DOCUMENTS**

	Document Number Country Code-Number-Kind Code	Date MM-YYYY <sup>1</sup>	Name	Classification <sup>2</sup>	
A	6,190,975	2/01	Kubo et al	438	285
B	2001/0160605	10/02	Kanazawa et al	438	689
C	5,683,934	11/97	Candelaria et al	438	----
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**FOREIGN PATENT DOCUMENTS**

	Document Number Country Code-Number-Kind Code	Date MM-YYYY <sup>1</sup>	Country	Name	Classification <sup>2</sup>	
N						
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**NON-PATENT DOCUMENTS**

	Include, as applicable: Author, Title, Date, Publisher, Edition or Volume, Pertinent Pages
U	Todd et al, "growth of heteroepitaxial SiGeC alloys on silicon using novel chemistry.", Appl. Phys. Lett. 67 9(1) 28 August 1995
V	
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\* A copy of this reference is not being furnished with this Office action. See MPEP § 707.05(a).

<sup>1</sup> Dates in MM-YYYY format are publication dates.<sup>2</sup> Classifications may be U.S. or foreign.